

60V NPN LOW SATURATION MEDIUM POWER TRANSISTOR IN SOT89

Features

- BV_{CEO} > 60V
- I_C = 5A High Continuous Current
- R_{SAT} = 30mΩ for a Low Equivalent On-Resistance
- Low Saturation Voltage V_{CE(SAT)} < 65mV @ I_C = 1A
- h_{FE} Specified Up to 10A for High Current Gain Hold Up
- Complementary PNP Type: ZXTP2012Z
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208(3)
- Weight: 0.05 grams (Approximate)

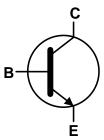
Application

- Emergency Lighting Circuits
- Motor Driving (Including DC Fans)
- · Backlight Inverters
- Power Switches
- Gate Driving MOSFETs and IGBTs

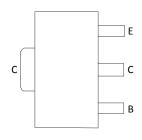




Top View



Device Symbol



Top View Pin Out

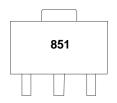
Ordering Information (Note 5)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXTN2010ZTA	AEC-Q101	851	7	12	1,000
ZXTN2010Z-13R	AEC-Q101	851	13	12	4,000
ZXTN2010ZQTA	Automotive	851	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



851 = Product Type Marking Code



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	150	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V _{EBO}	7	V
Base Current	I _B	2	Α
Continuous Collector Current	Ic	5	Α
Peak Pulse Current	I _{CM}	20	А

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6) Linear Derating Factor	P _D	1.5 12	W mW/°C
Power Dissipation (Note 7) Linear Derating Factor	P _D	2.1 16.8	W mW/°C
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	83	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	$R_{\theta JA}$	60	°C/W
Thermal Resistance, Junction to Leads (Note 8)	R _{0JL}	3.23	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	≥ 4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	С

Notes:

- 6. For a device mounted with the exposed collector pad on 25mm x 25mm 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.

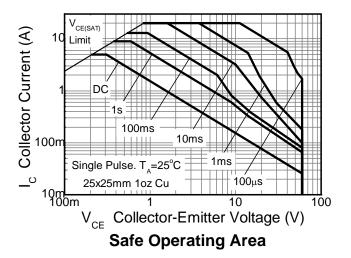
 7. Same as note (6), except the device is mounted on 50mm x 50mm 1oz copper.

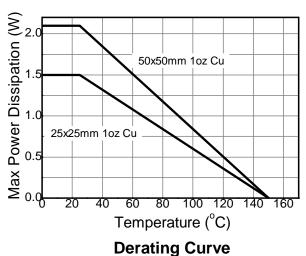
 8. Thermal resistance from junction to solder-point (on the exposed collector pad).

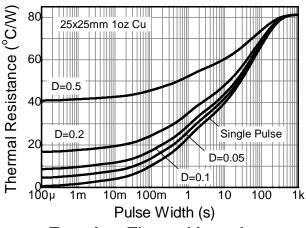
 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

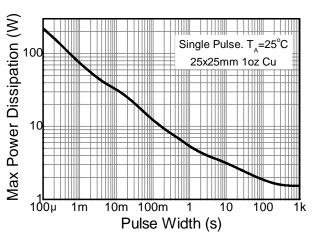


Thermal Characteristics and Derating Information









Transient Thermal Impedance

Pulse Power Dissipation



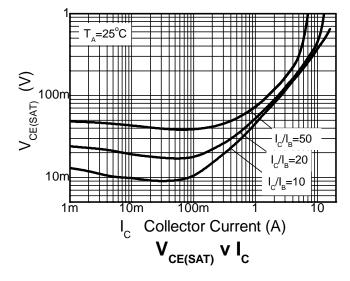
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

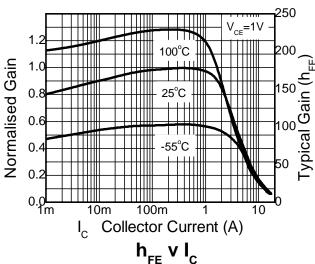
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	150	190	_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CER}	150	190	_	V	$I_C = 1\mu A, R_B \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	60	80	_	V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.1	_	V	$I_E = 100\mu A$
Collector Cutoff Current	I _{CBO}	_	< 1	50 500	nA nA	V _{CB} = 120V V _{CB} = 120V, T _A = +100°C
Collector Cutoff Current	I _{CER} R≤1kΩ	_	< 1	100 500	nA nA	V _{CB} = 120V V _{CB} = 120V, T _A = +100°C
Emitter Cutoff Current	I _{EBO}	_	< 1	10	nA	$V_{EB} = 6V$
		100	200	_	_	$I_C = 10$ mA, $V_{CE} = 1$ V
DC Current Transfer Static Ratio (Note 10)	h _{FE}	100	200	300		$I_C = 2A$, $V_{CE} = 1V$
De Current Transfer Static Natio (Note 10)		55	105	_		$I_C = 5A$, $V_{CE} = 1V$
		20	40	_		$I_C = 10A, V_{CE} = 1V$
		_	17	30	mV	$I_C = 100 \text{mA}, I_B = 5 \text{mA}$
	VCE(SAT)	_	35	55		$I_C = 1A$, $I_B = 100mA$
Collector-Emitter Saturation Voltage (Note 10)		_	40	65		$I_C = 1A$, $I_B = 50mA$
		_	90	125		$I_C = 2A$, $I_B = 50mA$
		_	170	230		$I_C = 6A, I_B = 300mA$
Base-Emitter Saturation Voltage (Note 10)	V _{BE(SAT)}	_	970	1100	mV	$I_C = 6A, I_B = 300mA$
Base-Emitter Turn-on Voltage (Note 10)	V _{BE(ON)}	_	910	1050	mV	$I_C = 6A$, $V_{CE} = 1V$
Transitional Frequency	f⊤	_	130	_	MHz	$I_C = 100 \text{mA}, V_{CE} = 10 \text{V},$ f = 50MHz
Output Capacitance	C _{OBO}	_	31	_	pF	$V_{CB} = 10V$, $f = 1MHz$,
Switching Time	t _{ON}		42		ns	$V_{CC} = 10V, I_C = 1A$
Switching fillie	t _{OFF}		760		115	$I_{B1} = -I_{B2} = 100 \text{mA}$

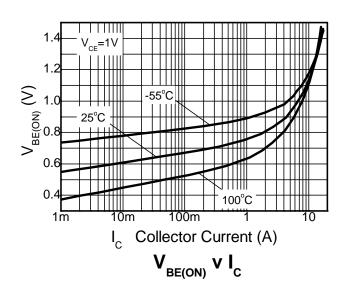
Note: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

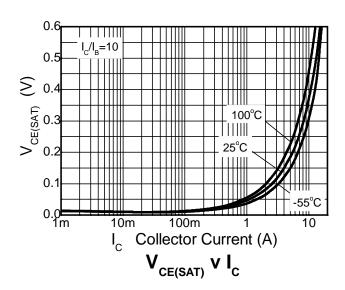


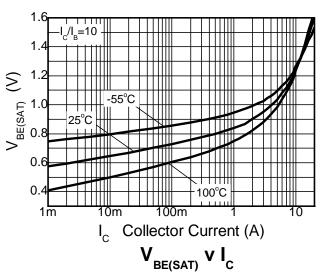
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)









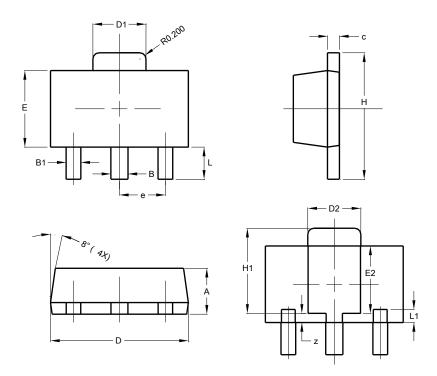




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89

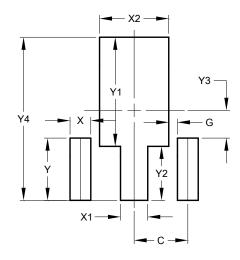


SOT89					
Dim	Min	Max	Тур		
Α	1.40	1.60	1.50		
В	0.50	0.62	0.56		
B1	0.42	0.54	0.48		
С	0.35	0.43	0.38		
D	4.40	4.60	4.50		
D1	1.62	1.83	1.733		
D2	1.61	1.81	1.71		
E	2.40	2.60	2.50		
E2	2.05	2.35	2.20		
е	-	-	1.50		
Н	3.95	4.25	4.10		
H1	2.63	2.93	2.78		
L	0.90	1.20	1.05		
L1	0.327	0.527	0.427		
Z	0.20	0.40	0.30		
All	All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89



Dimensions	Value (in mm)
С	1.500
G	0.244
X	0.580
X1	0.760
X2	1.933
Υ	1.730
Y1	3.030
Y2	1.500
Y3	0.770
Y4	4.530



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